



SANYO Semiconductors

# DATA SHEET

## LV5044V — Bi-CMOS IC 2ch step-down circuit DC-DC Converter Controller

### Overview

The LV5044V is a high efficiency, 2-channel, step-down, DC-DC converter controller IC adopting a synchronous rectifying system. Incorporating numerous functions on a single chip with easy external setting, it can be used for a wide variety of applications. The device is optimal for use in multi-output power supply systems which are used in LCD-TVs, DVD recorders, game machines, high-end office products, etc.

### Features

- Provides dual step-down DC-DC converter controller circuits integrated on the same chip.
- Provides an input UVLO circuit, an overcurrent detection function, an overtemperature detection function, soft start/soft stop functions, and a startup delay circuit.
- Output voltage monitoring functions (power good as well as OVP and UVP with timer latch functions)
- 180° interleaved operation between phase 1 and phase 2 (supports multiphase drive in 2-phase parallel operation mode).
- Supports synchronous operation between different devices (supports master/slave operation when multiple devices are used).

### Specifications

#### Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	$V_{IN}$		18	V
Peak output current	$I_{OUT}$		$\pm 1.0$	A
Allowable power dissipation	$P_d \text{ max}$	*1	1	W
Operating temperature	$T_{opr}$		-20 to +85	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-55 to +150	$^\circ\text{C}$

\*1 Board size:  $114.3 \times 76.1 \times 1.6 \text{ mm}^3$ , glass epoxy board.

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Parameter	Symbol	Conditions	Ratings	Unit
Allowable pin voltage *2				
1 HDRV1,2 CBOOT1,2			18	V
2 HDRV1,2 ,CBOOT1,2 to SW			6.5	V
3 $V_{IN}$ , ILIM1,2 RSNS1,2, SW1,2 PGOOD1,2			18	V
4 VLIN5 $V_{DD}$ , LDRV1,2			6.5	V
5 COMP1,2, FB1,2 SS1,2, UV_DELAY TD1,2, CT CLKO			VLIN5+0.3	V

\*2 Allowable pin voltages are referenced to the SGND and PGND pins, excluding No.2. No.2 Voltages are referenced to the SW pin.

## Recommended Operating Conditions at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	$V_{IN}$	$V_{IN}$ and VLIN open.	7.5 to 16	V
	$V_{IN}$	$V_{IN}$ and VLIN short.	4.5 to 6.0	V

## Electrical Characteristics at $T_a = 25^\circ\text{C}$ , $V_{IN} = 12\text{V}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
System						
Comparator reference voltage	V <sub>REF</sub>		0.818	0.826	0.834	V
Current drain 1	I <sub>CC1</sub>	TD1, TD2 = 5V (Excluding Ciss charge.)	2	4	6	mA
Current drain 2	I <sub>CC2</sub>	TD1, TD2 = 0V	0.3	0.6	1.2	mA
5V supply voltage	V <sub>LIN5</sub>	I <sub>V<sub>LIN5</sub></sub> = 0 to 10mA	4.75	5.00	5.25	V
Overcurrent detection comparator offset	V <sub>CL<sub>OS</sub></sub>		-5		+5	mV
Overcurrent detection reference current	I <sub>CL</sub>	V <sub>IN</sub> = 10 to 14V	7.47	8.30	9.13	μA
Soft start source current	I <sub>SS<sub>SC</sub></sub>	TD1, TD2 = 5V	-1.8	-3.5	-7.0	μA
Soft start sink current	I <sub>SS<sub>SK</sub></sub>	TD1, TD2 = 0V	0.2	1.0		mA
Soft start clamp voltage	V <sub>SS<sub>TO</sub></sub>		1.2	1.6	2.0	V
UV_DELAY source current	I <sub>SC<sub>UVD</sub></sub>	UV_DELAY = 2V	-4.3	-8.6	-17.2	μA
UV_DELAY sink current	I <sub>SK<sub>UVD</sub></sub>	UV_DELAY = 2V	0.2	1.0		mA
UV_DELAY threshold voltage	V <sub>UVD</sub>		1.5	2.4	3.5	V
UV_DELAY operating voltage	V <sub>UVD op</sub>	100% at V <sub>FB</sub> = V <sub>REF</sub>	87	92	97	%
VUVP detection hysteresis	ΔV <sub>UVP</sub>			2		%
Overvoltage detection	V <sub>OVP</sub>	100% at V <sub>FB</sub> = V <sub>REF</sub>	112	117	122	%
Overvoltage detection delay time	V <sub>ODLY</sub>			1.0		μS
Output discharge transistor on-resistance	V <sub>SWON</sub>		5	10	20	Ω
Output Block						
CBOOT leakage current	I <sub>CBOOT</sub>	V <sub>CBOOT</sub> = V <sub>SW</sub> + 6.5V			10	μA
HDRVx and LDRVX source current	I <sub>SCDRV</sub>			1.0		A
HDRVx and LDRVX sink current	I <sub>SKDRV</sub>			1.0		A
HDRVx low side on-resistance	R <sub>HDRV</sub>	I <sub>OUT</sub> =500mA		1.5	2.5	Ω
LDRVx low side on-resistance	R <sub>LDRV</sub>	I <sub>OUT</sub> =500mA		1.5	2.5	Ω
Simultaneous on prevention dead time 1	T <sub>dead1</sub>	LDRV off → HDRV on		50		nS
Simultaneous on prevention dead time 2	T <sub>dead2</sub>	HDRV off → LDRV on		120		nS

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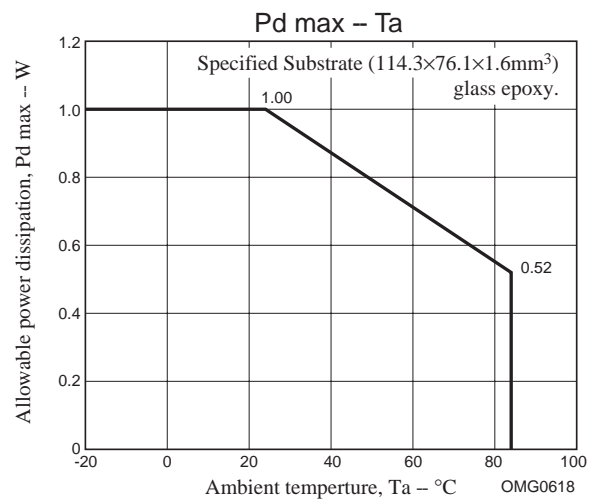
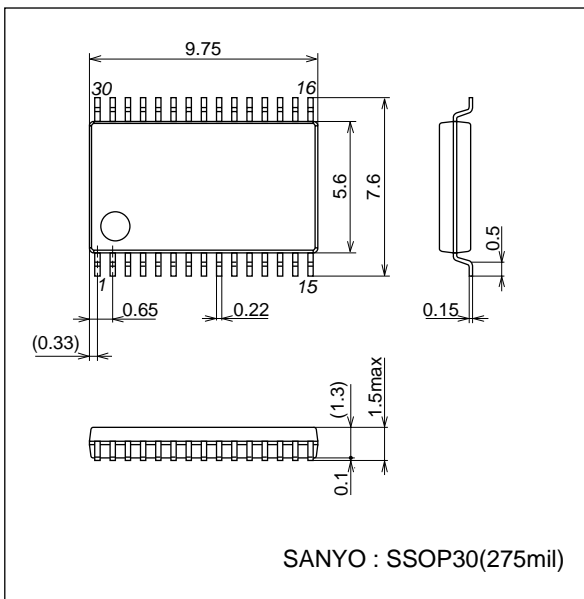
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Oscillator						
Oscillator frequency	f <sub>OSC</sub>	CT = 130pF	280	330	380	kHz
Oscillator frequency range	f <sub>OSC op</sub>		250		1100	kHz
Maximum on duty	D <sub>ON</sub> max	CT = 130pF	82			%
Minimum on time	T <sub>ON</sub> min	CT = 130pF		100		nS
Sawtooth wave high side voltage	V <sub>sawH</sub>	f <sub>OSC</sub> = 300kHz		2.2	2.6	V
Sawtooth wave low side voltage	V <sub>sawL</sub>	f <sub>OSC</sub> = 300kHz		1	1.2	V
On time difference between channels 1 and 2	ΔT <sub>dead</sub>			5		%
Error Amplifier						
Error amplifier input current	I <sub>FB</sub>		-200	-100	200	nA
COMP pin source current	I <sub>COMPSC</sub>			-100	-18	μA
COMP pin sink current	I <sub>COMPsk</sub>		18	100		μA
Error amplifier gm	gm		500	700	900	μmho
Current detection amplifier gain	G <sub>I</sub> SNS		1.5	2.0	2.5	dB
Logic Output						
Sink current in the power good low state	I <sub>pwrgdL</sub>	V <sub>PGOOD</sub> = 0.4V	0.5	1.0		mA
Leakage current in the power good high state	I <sub>pwrgdH</sub>	V <sub>PGOOD</sub> = 12V			10	μA
TD pin threshold level	V <sub>ONTD</sub>	When the TD pin is stepped up	1.5	2.4	3.5	V
TD pin open voltage	V <sub>TDH</sub>	V <sub>IN</sub> – V <sub>LIN5</sub> open.	4.5	5.0	5.5	V
TD pin source current during charge	I <sub>TDSC</sub>		-1.8	-3.5	-7.0	μA
TD pin sink current during discharge	I <sub>TDsk</sub>		0.8	2	5	mA
CLKO high-level voltage	V <sub>CLKOH</sub>	I <sub>CLKO</sub> = 1mA	0.7V <sub>LIN5</sub>			V
CLKO low-level voltage	V <sub>CLKOL</sub>	I <sub>CLKO</sub> = 1mA			0.3V <sub>LIN5</sub>	V
Protection Functions						
V <sub>IN</sub> UVLO release voltage	V <sub>UVLO</sub>		3.5	4.1	4.3	V
UVLO hysteresis	ΔV <sub>UVLO</sub>			0.2		V

## Package Dimensions

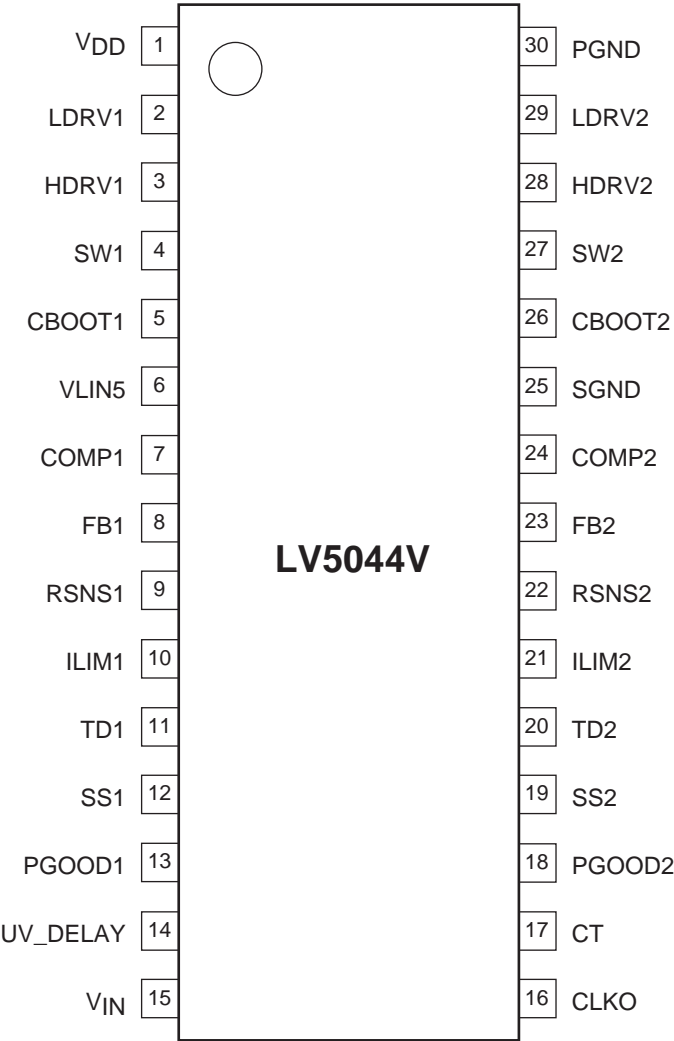
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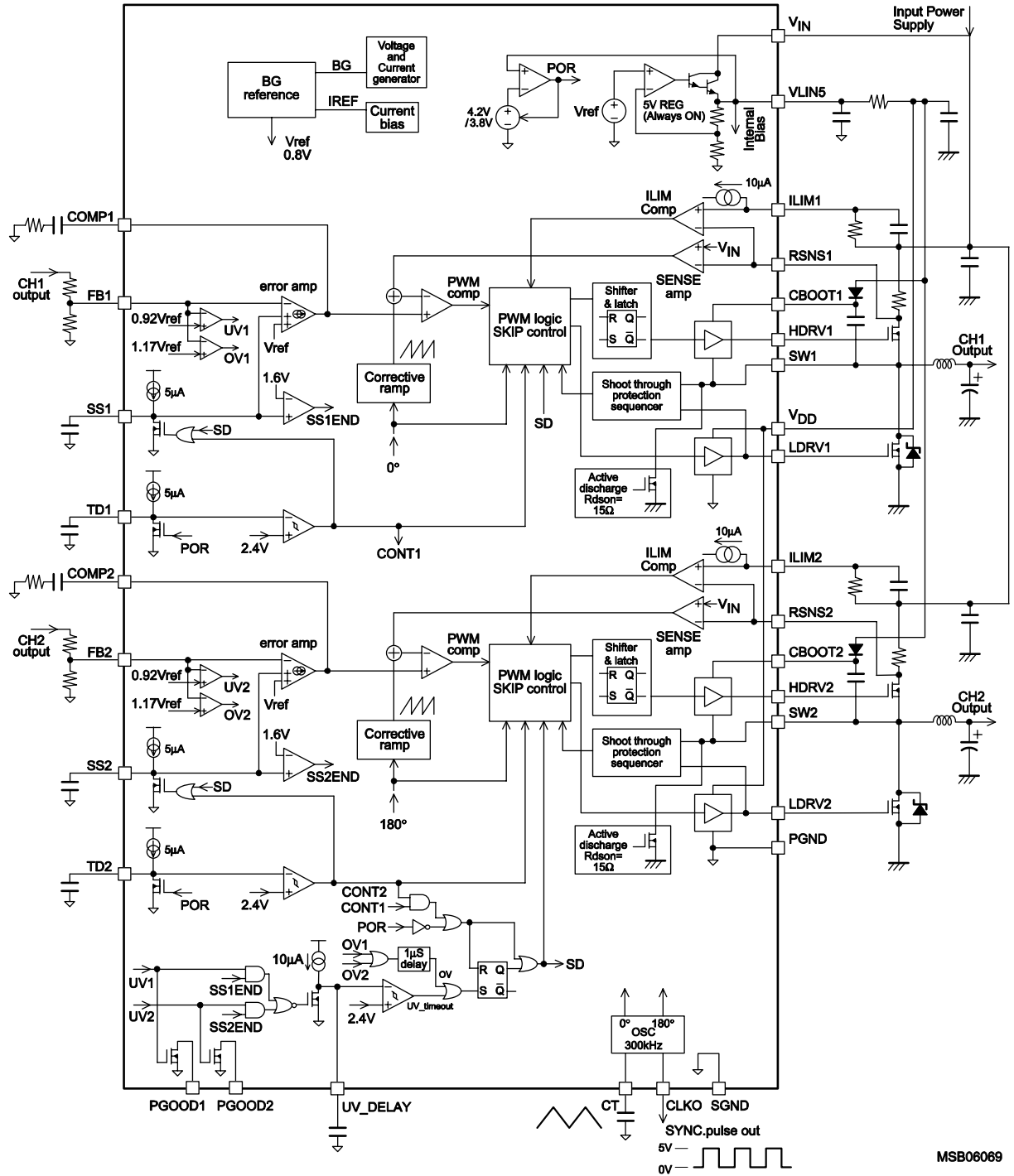
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Pin Assignment



Top view

# Block Diagram and Sample Application Circuit



MSB06069

## Pin Functions

Pin No.	Pin	Function
1	V <sub>DD</sub>	Gate drive power supply for the external low side MOSFETs. Connect this pin to VLIN5 through a filter.
2	LDRV1	Channel 1 external low side MOSFET gate drive. This pin is also used as the signal input for short through prevention for the high and low side MOSFETs. HDRV cannot be turned on unless this pin's voltage goes below 1V.
3	HDRV1	Channel 1 external high side MOSFET gate drive.
4	SW1	This pin is connected to the channel 1 switching node. The external high side MOSFET source and the low side MOSFET drain are connected to this pin. This pin becomes the return current route of pin HDRV. The drain of the discharging MOSFET used for the soft stop function is connected internal in the IC (typ. 15Ω). This pin is also used as the signal input for short through prevention for the high and low side MOSFETs. LDRV cannot be turned on unless this pin's voltage goes below 1V referenced to PGND.
5	CBOOT1	Channel 1 bootstrap capacitor connection. The high side MOSFET gate drive power is supplied from this pin. This pin is connected to V <sub>DD</sub> through a diode and to SW1 through the bootstrap capacitor.
6	VLIN5	Internal 5V regulator output. The current is supplied from V <sub>IN</sub> . The power supply for the IC internal control circuits is also supplied from this pin. A bypass capacitor (6.8μF) is required between this pin and SGND. This pin is monitored by the UVLO function and the IC starts operating when it first rises above 4.0V. (After starting, the IC will only stop if this voltage falls below 3.8V.)
7	COMP1	Channel 1 phase compensation. The output of the internal transconductance amplifier is connected to this pin. The external phase compensation circuit between this pin and SGND.
8	FB1	Channel 1 feedback input. The transconductance amplifier inverting (–) input is connected to this pin. Provide the feedback potential to this pin by voltage dividing the output voltage. The converter operates so that this pin goes to the internal reference voltage V <sub>REF</sub> , 0.8V. This pin is also monitored by both the UVP comparator and the OVP comparator. If this pin voltage falls to under 87% of the set voltage, the PGOOD1 pin will go low and the UV_TIMER will operate. If this pin voltage rises to over 117% of the set voltage, the IC will latch in the off state.
9	RSNS1	Input for the channel 1 side overcurrent detection comparator and current detection amplifier. When resistor detection is used, connect the low side of the current detection resistor inserted between V <sub>IN</sub> and the drain of the external high side MOSFET to this pin. These connections must be wired independently so that the shared impedance with the main current with respect to the detected voltage does not affect this circuit.
10	ILIM1	Connection to the channel 1 overcurrent detection trip point. A 8.3μA (ILIM) sink constant-current supply is connected internal in the IC, and the overcurrent detection voltage ILIM × RLIM is generated by connecting the resistor RLIM between this pin and V <sub>IN</sub> . The voltage between V <sub>IN</sub> and ILIM is compared to the voltage across the terminals of either the current detection resistor RSNS or the high side MOSFET to detect the overcurrent state.
11	TD1	Channel 1 startup delay connection. The time until the IC starts up after the power-on reset (POR) is cleared is set by the capacitor connected between this pin and SGND. After the POR state is cleared, the external capacitor is charged by a 3.5μA constant current supplied internally by the IC. The IC starts operation when the voltage on this pin exceeds 2.4V. The IC goes to the standby state when the voltage on this pin is under 2.4V. If no external capacitor is connected to this pin, the IC will start as soon as the power-on reset is cleared.
12	SS1	Channel 1 soft start capacitor connection. After the power-on reset (POR) is cleared and the TD pin voltage exceeds 2.4V, this capacitor is charged by a 3.5μA internal constant current supply from the SS1 pin. This pin is connected to the transconductance amplifier's noninverting (+) input, and the ramp waveform of the SS1 pin is reflected in the ramped-up output waveform. After the UV_DELAY time out and the POR operates, this capacitor is discharged by the SS pin.
13	PGOOD1	Channel 1 power good pin. An IC internal 28V MOSFET open drain is connected to this pin. This pin outputs a low level if the channel 1 output voltage falls more than -13% relative to the set voltage. There is a hysteresis of about V <sub>REF</sub> × 1.5%.
14	UV_DELAY	Channel 1 and channel 2 common UVP delay connection. The time until the IC switches off after the UVP state is detected is set by the capacitor connected between this pin and SGND. If either the channel 1 or channel 2 output voltage falls under -80% of the set voltage, an IC internal 8.6μA constant current source charges the external capacitor connected to this pin. When the voltage on this pin exceeds 2.4V, the IC switches off. If no external capacitor is connected, the IC turns off immediately upon detection of the UVP state.
15	V <sub>IN</sub>	IC power supply.
16	CLKO	Clock output. This pin outputs a clock signal synchronized with the CT pin oscillator waveform. When two or more LV5044V chips are operated in synchronization, connect the CT pin of the slave device to the SLKO pin of the master device. If two or more devices are operated in synchronization and the Td pin is used to change the startup timing between the devices, the device that starts the soonest will be the master.

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Pin No.	Pin	Function
17	CT	Connection for the oscillator circuit's external capacitor. Connect that capacitor between this pin and ground. When CT is 130pF, $f_{OSC}$ will be 330kHz. If an external clock is applied to this pin, the PWM control functions will operate at that clock frequency. If an external clock is provided, that signal must be a square wave with a low level of 0V and a high level between 3.3 and 5.0V. The square wave generator must have a fanout drive capacity of at least 1mA. and UV_DELAY function doesn't operate when this pin is grounded.
18	PGOOD2	Channel 2 power good pin.
19	SS2	Channel 2 soft start function capacitor connection.
20	TD2	Channel 2 startup delay connection.
21	ILIM2	Channel 2 overcurrent detection trip point setting.
22	RSNS1	Channel 2 overcurrent detection comparator input.
23	FB2	Channel 2 feedback input.
24	COMP2	Channel 2 phase compensation.
25	SGND	IC system ground. The reference voltage is generated referenced to this pin. The system ground must be connected to this pin.
26	CBOOT2	Channel 2 bootstrap capacitor connection.
27	SW2	This pin is connected to the channel 2 switching node.
28	HDRV2	Channel 2 external high side MOSFET gate drive.
29	LDRV2	Channel 2 external low side MOSFET gate drive.
30	PGND	Power system ground. This pin is used as the current return path for the LDRV pin.

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